

WBFBP-03B Plastic-Encapsulate Diode

DAN222M SWITCHING DIODE

DESCRIPTION

Epitaxial planar Silicon diode

FEATURES: BACK

High speed. ($t_{rr}=1.5\text{ns}$ Typ.)

Suitable for high packing density layout

High reliability.

APPLICATION

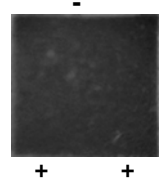
Ultra high speed switching

For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM, DVD-ROM, Note book PC, etc.)

WBFBP-03B

(1.2×1.2×0.5)
unit: mm

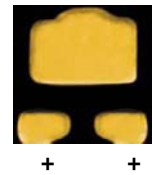
TOP



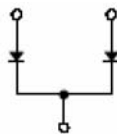
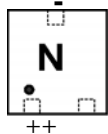
1. ANODE

2. ANODE

3.CATHODE



MARKING:

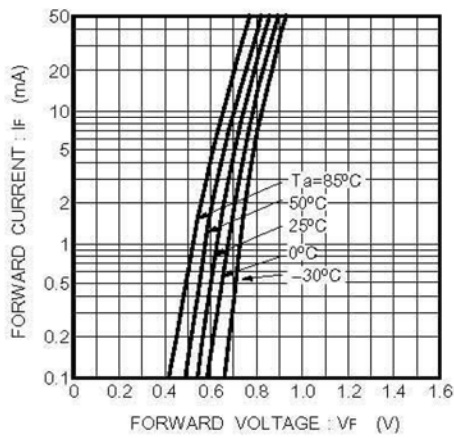


Maximum Ratings and Electrical Characteristics, Single Diode @ $T_A=25^\circ\text{C}$

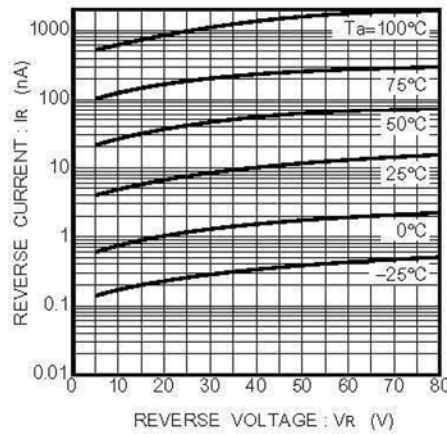
Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	80	V
DC reverse voltage	V_R	80	V
Maximum (peak) forward current	I_{FM}	300	mA
Average forward current	I_o	100	mA
Power dissipation	P_D	150	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55-150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

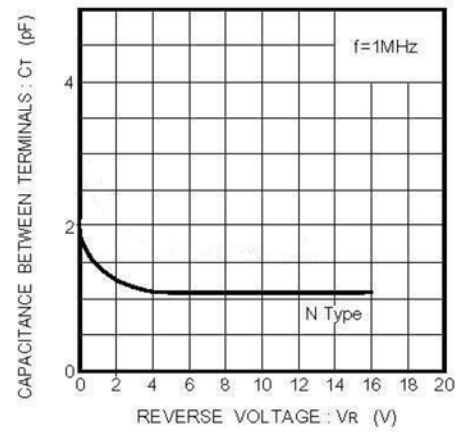
	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	80		V
Reverse voltage leakage current	I_R	$V_R=70\text{V}$		0.1	μA
Forward voltage	V_F	$I_F=100\text{mA}$		1.2	V
Diode capacitance	C_D	$V_R=6\text{V}$, $f=1\text{MHz}$		3.5	pF
Reverse recovery time	t_{rr}	$V_R=6\text{V}$, $I_F=5\text{mA}$		4	ns



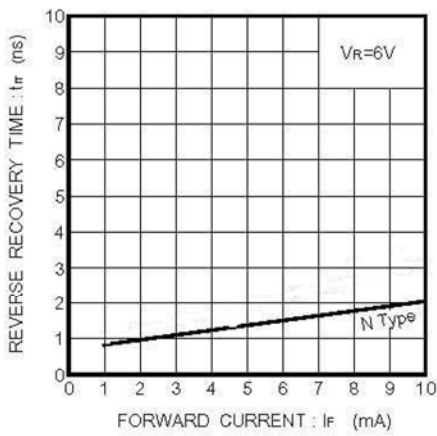
Forward characteristics



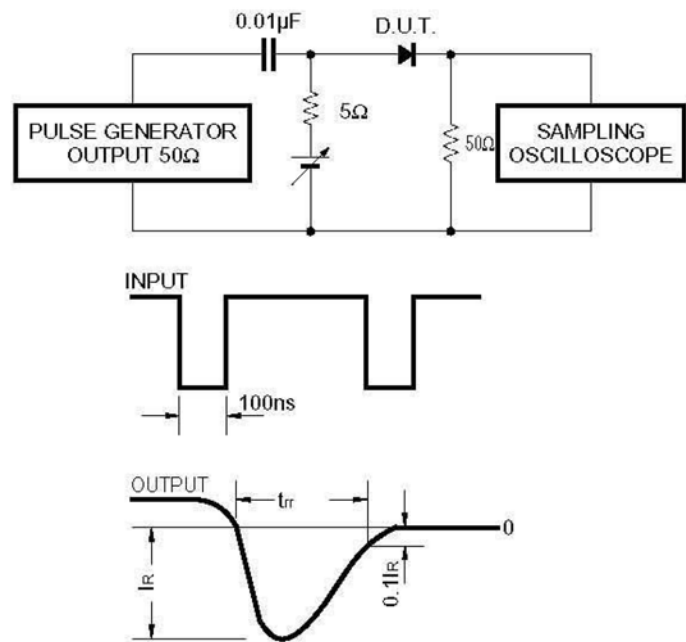
Reverse characteristics



Capacitance between terminals characteristics



Reverse recovery time



Reverse recovery time (t_{rr}) measurement circuit

